



Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 246179US90DIV		SERIAL NO. 10/734,221	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Hiroyuki NAGASAWA, et al.			
				FILING DATE December 15, 2003		GROUP 1775	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
SSS	AA	6,051,849	04-2000	DAVIS ET AL.			
SSS	AB	5,471,946	12-1995	SCHOLZ ET AL.			
SSS	AC	6,184,144	02-2001	LO			
SSS	AD	US005230768A	07-1993	FURUKAWA ET AL.			
SSS	AE	US005915194A	06-1999	POWELL ET AL.			
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SSS	AH	US005122223A	06-1992	GEIS ET AL.			
SSS	AI	4,946,547	08-1990	PALMOUR ET AL.			
SSS	AJ	4,912,064	05-1990	KONG ET AL.			
SSS	AK	US006596080B2	07-2003	KAWAHARA ET AL.			
SSS	AL	US20030047129A1	03-2003	KAWAHARA ET AL.			
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
SSS	AO	6-41400	06-1994	JAPAN (with English Abstract)		X	
SSS	AP	7-335562	12-1995	JAPAN (with partial English Abstract)			
SSS	AQ	EP0743727A1	11-1996	EUROPE			
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
SSS	AU	H. NAGASAWA ET AL., Materials Science Forum, Vols. 389-393, pgs 319-322, "HETEROEPITAZIAL GROWTH AND CHARACTERISTICS OF 3C-SiC ON LARGE-DIAMETER Si(001)SUBSTRATES," 2002					
SSS	AV	A. NAGAYAMA ET AL., Phys. Stat. Sol. (a), Vol. 176, pgs. 513-517, "SUBSTRATE MISORIENTATION DEPENDENCE OF THE HEXAGONAL PHASE INCLUSION IN CUBIC GaN FILMS GROWN BY METALORGANIC VAPOR PHASE EPITAXY," 1999					
SSS	AW	C. LONG ET AL., Journal of Applied Physics, Vol. 86, No. 5, pps. 2509-2515, XP-000934896, "STRUCTURAL DEFECTS IN 3C-SiC GROWN ON Si BY SUPERSONIC JET EPITAXY", September 1, 1999.					
SSS	AX	Y. V. MELNIK ET AL., Diamond and Related Materials, Vol. 6, No. 10, pgs. 1532-1535, XP-004096982, "STRUCTURAL PROPERTIES OF GaN GROWN ON SiC SUBSTRATES BY HYDRIDE VAPOR PHASE EPITAXY", August 1, 1997.				<input type="checkbox"/> Additional References sheet(s) attached	
SSS	AY	H. D. CHO ET AL., Journal of Crystal Growth, Vol. 175-175, No. 3001, pgs. 125-128, XP-004091279, "ZINC BLENDE GaN GROWN BY RADIO FREQUENCY PLASMA ASSISTED MOLECULAR BEAM EPITAXY", May 1, 1997.					
Examiner <i>Steph Slone</i>					Date Considered 9/30/2005		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							